

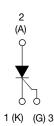
### VS-25TTS..FPPbF Series, VS-25TTS..FP-M3 Series

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Vishay Semiconductors

# **High Voltage Phase Control Thyristor, 25 A**





10-220AB FULL-PAK
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PRODUCT SUMMARY				
Package	TO-220FP			
Diode variation	Single SCR			
I <sub>T(AV)</sub>	16 A			
V <sub>DRM</sub> /V <sub>RRM</sub>	800 V, 1200 V			
$V_{TM}$	1.25 V			
I <sub>GT</sub>	45 mA			
T <sub>J</sub>	- 40 °C to 125 °C			

#### **FEATURES**

- · Designed and qualified for industrial level
- Fully isolated package (V<sub>INS</sub> = 2500 V<sub>RMS</sub>)
- UL E78996 pending
- Compliant to RoHS Directive 2002/95/EC
- 125 °C max. operating junction temperature
- Halogen-free according to IEC 61249-2-21 definition (-M3 only)





ROHS
COMPLIANT
HALOGEN
FREE
Available

#### **APPLICATIONS**

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

#### **DESCRIPTION**

The VS-25TTS...FP... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS					
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS		
Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C, common heatsink of 1 °C/W	18	22	А		

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I <sub>T(AV)</sub>	Sinusoidal waveform	16	٨		
I <sub>RMS</sub>		25	Α		
V <sub>RRM</sub> /V <sub>DRM</sub>		800/1200	V		
I <sub>TSM</sub>		300	A		
V <sub>T</sub>	16 A, T <sub>J</sub> = 25 °C	1.25	V		
dV/dt		500	V/µs		
dl/dt		150	A/µs		
TJ		- 40 to 125	°C		

VOLTAGE RATINGS						
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA			
VS-25TTS08FPPbF, VS-25TTS08FP-M3	800	800	10			
VS-25TTS12FPPbF, VS-25TTS12FP-M3	1200	1200	10			



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ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
	STINIBUL	TEST CONDITIONS	TYP. MAX.	
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 85 °C, 180° conduction half sine wave	16	
Maximum RMS on-state current	I <sub>RMS</sub>		25	Α
Maximum peak, one-cycle,	<b>L</b>	10 ms sine pulse, rated V <sub>RRM</sub> applied	300	_ ^
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no voltage reapplied	350	
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine pulse, rated V <sub>RRM</sub> applied	450	- A <sup>2</sup> s
waximum i-t for fusing	1-1	10 ms sine pulse, no voltage reapplied	630	A-5
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1ms to 10 ms, no voltage reapplied	6300	A²√s
Maximum on-state voltage drop	$V_{TM}$	16 A, T <sub>J</sub> = 25 °C	1.25	V
On-state slope resistance	r <sub>t</sub>	T <sub>.I</sub> = 125 °C	12.0	mΩ
Threshold voltage	V <sub>T(TO)</sub>	1j = 125 C	1.0	V
Maximum rayaraa and direct lookaga aurrant	1 /1	$T_J = 25 ^{\circ}\text{C}$	0.5	
Maximum reverse and direct leakage current	$I_{RM}/I_{DM}$	$T_{\rm J} = 125  ^{\circ}{\rm C}$ $V_{\rm R} = {\rm Rated}  {\rm V}_{\rm RRM} / {\rm V}_{\rm DRM}$	10	mA
Holding current	lΗ	Anode supply = 6 V, resistive load, initial I <sub>T</sub> = 1 A	- 100	IIIA
Maximum latching current	ΙL	Anode supply = 6 V, resistive load	200	
Maximum rate of rise of off-state voltage	dV/dt		500	V/µs
Maximum rate of rise of turned-on current	dl/dt		150	A/µs

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	$P_{GM}$		8.0	w	
Maximum average gate power	P <sub>G(AV)</sub>		2.0	] "	
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	Α	
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V	
	I <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	60		
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	45	mA	
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	20		
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	2.5		
Maximum required DC gate voltage to trigger	$V_{\mathrm{GT}}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	2.0	V	
voltage to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	1.0	]	
Maximum DC gate voltage not to trigger	$V_{GD}$	T = 125 °C V = Peted value	0.25		
Maximum DC gate current not to trigger	I <sub>GD</sub>	$T_J = 125 ^{\circ}\text{C},  V_{\text{DRM}} = \text{Rated value}$		mA	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9	
Typical reverse recovery time	t <sub>rr</sub>	T <sub>.I</sub> = 125 °C	4	μs
Typical turn-off time	t <sub>q</sub>	1 1 1 1 2 5 6	110	



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THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		T <sub>J</sub> , T <sub>Stg</sub>		- 40 to 125	°C
Maximum thermal resistance, junction to case		$R_{thJC}$	DC operation	1.5	
Maximum thermal resistance, junction to ambient		R <sub>thJA</sub>		62	°C/W
Typical thermal resistance, case to heatsink		R <sub>thCS</sub>	Mounting surface, smooth and greased	1.5	
Approximate weight				2	g
Approximate weight				0.07	oz.
Mounting torque ———	minimum			6 (5)	kgf · cm
	maximum			12 (10)	(lbf · in)
Marking dayion	Modernostrator		Occasional TO COOME FULL DAY (OANO)	25TTS08FP	
Marking device			Case style TO-220AB FULL-PAK (94/V0)	25TTS12FP	

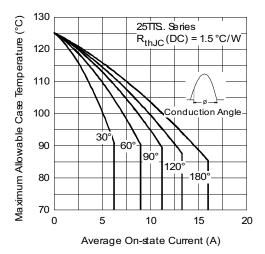


Fig. 1 - Current Rating Characteristics

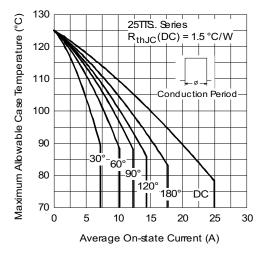


Fig. 2 - Current Rating Characteristics

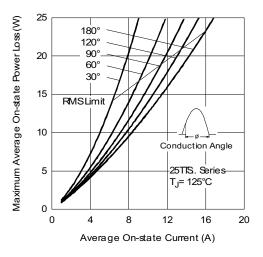


Fig. 3 - On-State Power Loss Characteristics

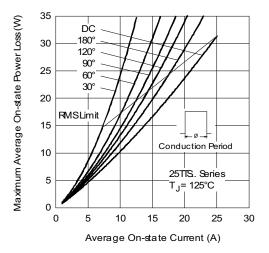


Fig. 4 - On-State Power Loss Characteristics

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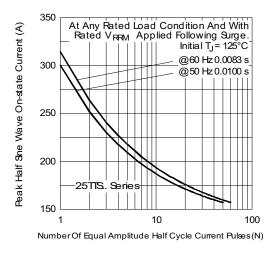


Fig. 5 - Maximum Non-Repetitive Surge Current

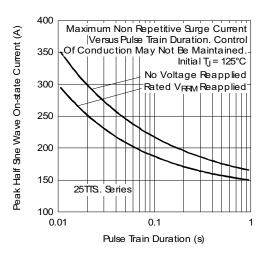


Fig. 6 - Maximum Non-Repetitive Surge Current

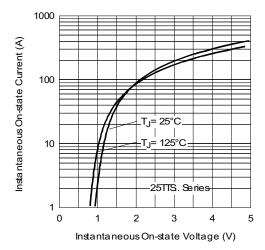


Fig. 7 - On-State Voltage Drop Characteristics

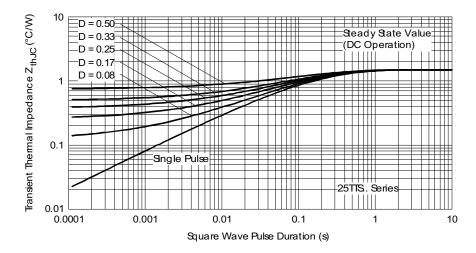


Fig. 8 - Thermal Impedance Z<sub>thJC</sub> Characteristics

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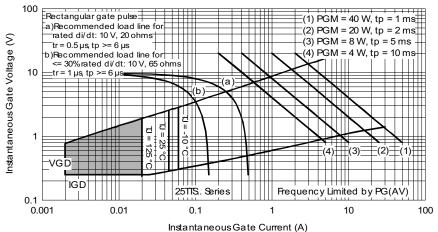
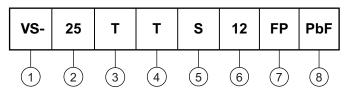


Fig. 9 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**

**Device code** 



Vishay Semiconductors product

Current rating (25 = 25 A)

Circuit configuration:

T = Single thyristor

Package:

T = TO-220AB

5 Type of silicon:

Standard recovery rectifier

08 = 800 V6 Voltage code x  $100 = V_{RRM}$ 12 = 1200 V

**FULL-PAK** 

8 Environmental digit:

PbF = Lead (Pb)-free and RoHS compliant

-M3 = Halogen-free, RoHS compliant, and terminations lead (Pb)-free

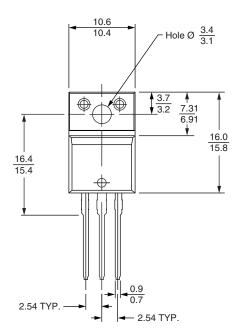
ORDERING INFORMATION (Example)				
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION	
VS-25TTS08FPPbF	50	1000	Antistatic plastic tubes	
VS-25TTS08FP-M3	50	1000	Antistatic plastic tubes	
VS-25TTS12FPPbF	50	1000	Antistatic plastic tubes	
VS-25TTS12FP-M3	50	1000	Antistatic plastic tubes	

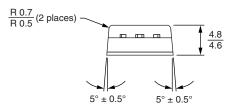
LINKS TO RELATED DOCUMENTS				
Dimensions		www.vishay.com/doc?95072		
Dout moulcing information	TO-220FP PbF	www.vishay.com/doc?95069		
Part marking information	TO-220FP -M3	www.vishay.com/doc?95456		

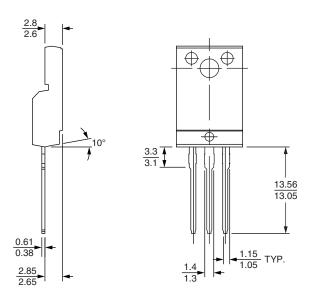


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### **DIMENSIONS** in millimeters







### Lead assignments

#### **Diodes**

- 1. Anode/open
- 2. Cathode
- 3. Anode

Conforms to JEDEC outline TO-220 FULL-PAK



### **Legal Disclaimer Notice**

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